

74LVC1G125

Bus buffer/line driver; 3-state

Rev. 11 — 2 July 2012

Product data sheet

1. General description

The 74LVC1G125 provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{OE}). A HIGH-level at pin \overline{OE} causes the output to assume a high-impedance OFF-state.

The input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- CMOS low power consumption
- Inputs accept voltages up to 5 V
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C



3. Ordering information

Table 1. Ordering information

| Type number | Package | | | Version |
|--------------|-------------------|--------|--|----------|
| | Temperature range | Name | Description | |
| 74LVC1G125GW | -40 °C to +125 °C | TSSOP5 | plastic thin shrink small outline package; 5 leads; body width 1.25 mm | SOT353-1 |
| 74LVC1G125GV | -40 °C to +125 °C | SC-74A | plastic surface-mounted package; 5 leads | SOT753 |
| 74LVC1G125GM | -40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm | SOT886 |
| 74LVC1G125GF | -40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm | SOT891 |
| 74LVC1G125GN | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm | SOT1115 |
| 74LVC1G125GS | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm | SOT1202 |
| 74LVC1G125GX | -40 °C to +125 °C | X2SON5 | X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.35 mm | SOT1226 |

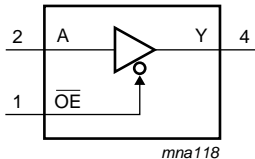

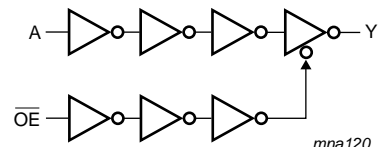
4. Marking

Table 2. Marking

| Type number | Marking code ^[1] |
|--------------|-----------------------------|
| 74LVC1G125GW | VM |
| 74LVC1G125GV | V25 |
| 74LVC1G125GM | VM |
| 74LVC1G125GF | VM |
| 74LVC1G125GN | VM |
| 74LVC1G125GS | VM |
| 74LVC1G125GX | VM |

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

| | | |
|--|--|--|
|  <p><i>mna118</i></p> |  <p><i>mna119</i></p> |  <p><i>mna120</i></p> |
| Fig 1. Logic symbol | Fig 2. IEC logic symbol | Fig 3. Logic diagram |

6. Pinning information

6.1 Pinning

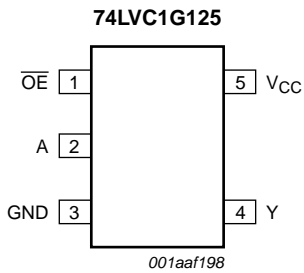


Fig 4. Pin configuration SOT353-1 and SOT753

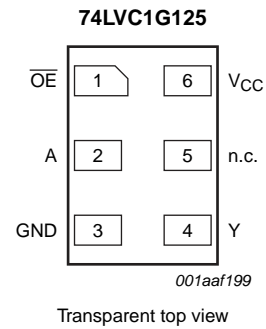


Fig 5. Pin configuration SOT886

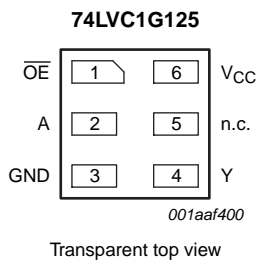


Fig 6. Pin configuration SOT891, SOT1115 and SOT1202

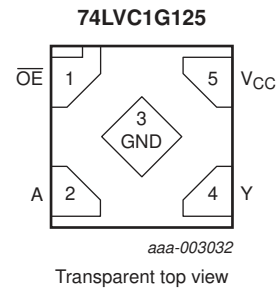


Fig 7. Pin configuration SOT1226 (X2SON5)

6.2 Pin description

Table 3. Pin description

| Symbol | Pin | | Description |
|-----------------|-------------------|-------|---------------------|
| | TSSOP5 and X2SON5 | XSON6 | |
| \overline{OE} | 1 | 1 | output enable input |
| A | 2 | 2 | data input |
| GND | 3 | 3 | ground (0 V) |
| Y | 4 | 4 | data output |
| n.c. | - | 5 | not connected |
| V _{CC} | 5 | 6 | supply voltage |

7. Functional description

Table 4. Function table^[1]

| Input | | Output |
|-------|---|--------|
| OE | A | Y |
| L | L | L |
| L | H | H |
| H | X | Z |

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|-------------------------------|------------------------|----------------|------|
| V_{CC} | supply voltage | | -0.5 | +6.5 | V |
| I_{IK} | input clamping current | $V_I < 0$ V | -50 | - | mA |
| V_I | input voltage | | ^[1] -0.5 | +6.5 | V |
| I_{OK} | output clamping current | $V_O > V_{CC}$ or $V_O < 0$ V | - | ±50 | mA |
| V_O | output voltage | Active mode | ^{[1][2]} -0.5 | $V_{CC} + 0.5$ | V |
| | | Power-down mode | ^{[1][2]} -0.5 | +6.5 | V |
| I_O | output current | $V_O = 0$ V to V_{CC} | - | ±50 | mA |
| I_{CC} | supply current | | - | 100 | mA |
| I_{GND} | ground current | | -100 | - | mA |
| P_{tot} | total power dissipation | $T_{amb} = -40$ °C to +125 °C | ^[3] - | 250 | mW |
| T_{stg} | storage temperature | | -65 | +150 | °C |

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.
 [3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
 For XSON6 and X2SON5 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------------------------|---------------------------------|------|-----|----------|------|
| V_{CC} | supply voltage | | 1.65 | - | 5.5 | V |
| V_I | input voltage | | 0 | - | 5.5 | V |
| V_O | output voltage | Active mode | 0 | - | V_{CC} | V |
| | | $V_{CC} = 0$ V; Power-down mode | 0 | - | 5.5 | V |
| T_{amb} | ambient temperature | | -40 | - | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 1.65$ V to 2.7 V | - | - | 20 | ns/V |
| | | $V_{CC} = 2.7$ V to 5.5 V | - | - | 10 | ns/V |

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ ^[1] | Max | Unit |
|--|---------------------------|---|----------------------|--------------------|----------------------|---------|
| $T_{amb} = -40$ °C to +85 °C | | | | | | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | $0.65 \times V_{CC}$ | - | - | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | 1.7 | - | - | V |
| | | $V_{CC} = 2.7$ V to 3.6 V | 2.0 | - | - | V |
| | | $V_{CC} = 4.5$ V to 5.5 V | $0.7 \times V_{CC}$ | - | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | - | - | $0.35 \times V_{CC}$ | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | - | - | 0.7 | V |
| | | $V_{CC} = 2.7$ V to 3.6 V | - | - | 0.8 | V |
| | | $V_{CC} = 4.5$ V to 5.5 V | - | - | $0.3 \times V_{CC}$ | V |
| V_{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $V_{CC} = 1.65$ V to 5.5 V; $I_O = 100$ μ A | - | - | 0.1 | V |
| | | $V_{CC} = 1.65$ V; $I_O = 4$ mA | - | - | 0.45 | V |
| | | $V_{CC} = 2.3$ V; $I_O = 8$ mA | - | - | 0.3 | V |
| | | $V_{CC} = 2.7$ V; $I_O = 12$ mA | - | - | 0.4 | V |
| | | $V_{CC} = 3.0$ V; $I_O = 24$ mA | - | - | 0.55 | V |
| V_{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $V_{CC} = 1.65$ V to 5.5 V; $I_O = -100$ μ A | $V_{CC} - 0.1$ | - | - | V |
| | | $V_{CC} = 1.65$ V; $I_O = -4$ mA | 1.2 | - | - | V |
| | | $V_{CC} = 2.3$ V; $I_O = -8$ mA | 1.9 | - | - | V |
| | | $V_{CC} = 2.7$ V; $I_O = -12$ mA | 2.2 | - | - | V |
| | | $V_{CC} = 3.0$ V; $I_O = -24$ mA | 2.3 | - | - | V |
| I_I | input leakage current | $V_{CC} = 0$ V to 5.5 V; $V_I = 5.5$ V or GND | - | ± 0.1 | ± 5 | μ A |
| | | $V_{CC} = 3.6$ V; $V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5$ V or GND | - | ± 0.1 | ± 10 | μ A |

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ ^[1] | Max | Unit |
|--|---------------------------|--|----------------------|--------------------|----------------------|---------------|
| I_{OFF} | power-off leakage current | $V_{CC} = 0\text{ V}$; V_I or $V_O = 5.5\text{ V}$ | - | ± 0.1 | ± 10 | μA |
| I_{CC} | supply current | $V_I = 5.5\text{ V}$ or GND; $V_{CC} = 1.65\text{ V}$ to 5.5 V ; $I_O = 0\text{ A}$ | - | 0.1 | 10 | μA |
| ΔI_{CC} | additional supply current | per pin; $V_{CC} = 2.3\text{ V}$ to 5.5 V ; $V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$ | - | 5 | 500 | μA |
| C_I | input capacitance | | - | 5 | - | pF |
| $T_{amb} = -40\text{ }^\circ\text{C}$ to $+125\text{ }^\circ\text{C}$ | | | | | | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 1.65\text{ V}$ to 1.95 V | $0.65 \times V_{CC}$ | - | - | V |
| | | $V_{CC} = 2.3\text{ V}$ to 2.7 V | 1.7 | - | - | V |
| | | $V_{CC} = 2.7\text{ V}$ to 3.6 V | 2.0 | - | - | V |
| | | $V_{CC} = 4.5\text{ V}$ to 5.5 V | $0.7 \times V_{CC}$ | - | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 1.65\text{ V}$ to 1.95 V | - | - | $0.35 \times V_{CC}$ | V |
| | | $V_{CC} = 2.3\text{ V}$ to 2.7 V | - | - | 0.7 | V |
| | | $V_{CC} = 2.7\text{ V}$ to 3.6 V | - | - | 0.8 | V |
| | | $V_{CC} = 4.5\text{ V}$ to 5.5 V | - | - | $0.3 \times V_{CC}$ | V |
| V_{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $V_{CC} = 1.65\text{ V}$ to 5.5 V ; $I_O = 100\text{ }\mu\text{A}$ | - | - | 0.1 | V |
| | | $V_{CC} = 1.65\text{ V}$; $I_O = 4\text{ mA}$ | - | - | 0.70 | V |
| | | $V_{CC} = 2.3\text{ V}$; $I_O = 8\text{ mA}$ | - | - | 0.45 | V |
| | | $V_{CC} = 2.7\text{ V}$; $I_O = 12\text{ mA}$ | - | - | 0.60 | V |
| | | $V_{CC} = 3.0\text{ V}$; $I_O = 24\text{ mA}$ | - | - | 0.80 | V |
| V_{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $V_{CC} = 1.65\text{ V}$ to 5.5 V ; $I_O = -100\text{ }\mu\text{A}$ | $V_{CC} - 0.1$ | - | - | V |
| | | $V_{CC} = 1.65\text{ V}$; $I_O = -4\text{ mA}$ | 0.95 | - | - | V |
| | | $V_{CC} = 2.3\text{ V}$; $I_O = -8\text{ mA}$ | 1.7 | - | - | V |
| | | $V_{CC} = 2.7\text{ V}$; $I_O = -12\text{ mA}$ | 1.9 | - | - | V |
| | | $V_{CC} = 3.0\text{ V}$; $I_O = -24\text{ mA}$ | 2.0 | - | - | V |
| I_I | input leakage current | $V_{CC} = 0\text{ V}$ to 5.5 V ; $V_I = 5.5\text{ V}$ or GND | - | - | ± 100 | μA |
| | | $V_{CC} = 3.6\text{ V}$; $V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5\text{ V}$ or GND | - | - | ± 200 | μA |
| I_{OFF} | power-off leakage current | $V_{CC} = 0\text{ V}$; V_I or $V_O = 5.5\text{ V}$ | - | - | ± 200 | μA |
| I_{CC} | supply current | $V_I = 5.5\text{ V}$ or GND; $V_{CC} = 1.65\text{ V}$ to 5.5 V ; $I_O = 0\text{ A}$ | - | - | 200 | μA |
| ΔI_{CC} | additional supply current | per pin; $V_{CC} = 2.3\text{ V}$ to 5.5 V ; $V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$ | - | - | 5000 | μA |

[1] All typical values are measured at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^\circ\text{C}$.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 10](#).

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|------------------|-------------------------------|--|------------------|--------------------|-----|-------------------|------|------|
| | | | Min | Typ ^[1] | Max | Min | Max | |
| t _{pd} | propagation delay | A to Y; see Figure 8 ^[2] | | | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.0 | 3.3 | 8.0 | 1.0 | 10.5 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 0.5 | 2.2 | 5.5 | 0.5 | 7 | ns |
| | | V _{CC} = 2.7 V | 0.5 | 2.5 | 5.5 | 0.5 | 7 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | 2.1 | 4.5 | 0.5 | 6 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | 1.7 | 4.0 | 0.5 | 5.5 | ns |
| t _{en} | enable time | OE to Y; see Figure 9 ^[3] | | | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.0 | 4.1 | 9.4 | 1.0 | 12 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 0.5 | 2.8 | 6.6 | 0.5 | 8.5 | ns |
| | | V _{CC} = 2.7 V | 0.5 | 3.3 | 6.6 | 0.5 | 8.5 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | 2.4 | 5.3 | 0.5 | 7 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | 2.1 | 5.0 | 0.5 | 6.5 | ns |
| t _{dis} | disable time | OE to Y; see Figure 9 ^[4] | | | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.0 | 4.3 | 9.2 | 1.0 | 12 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 0.5 | 2.7 | 5.0 | 0.5 | 6.5 | ns |
| | | V _{CC} = 2.7 V | 0.5 | 3.0 | 5.0 | 0.5 | 6.5 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | 3.1 | 5.0 | 0.5 | 6.5 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | 2.2 | 4.2 | 0.5 | 5.5 | ns |
| C _{PD} | power dissipation capacitance | per buffer; V _I = GND to V _{CC} ^[5] | | | | | | |
| | | output enabled | - | 25 | - | - | - | pF |
| | | output disabled | - | 6 | - | - | - | pF |

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] t_{en} is the same as t_{PZH} and t_{PZL}

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ}

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

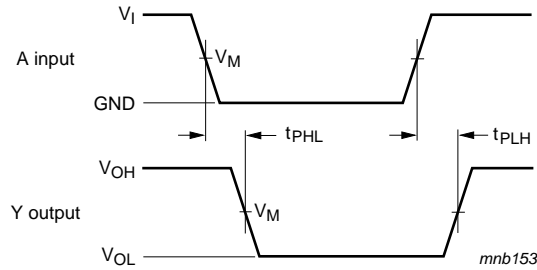
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

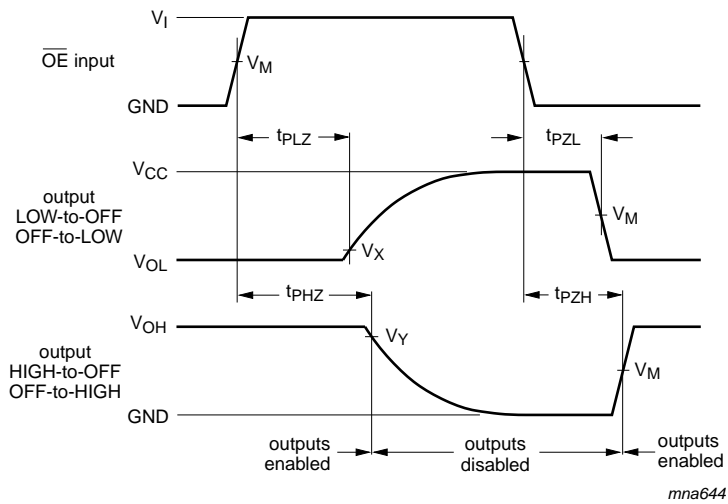
∑(C_L × V_{CC}² × f_o) = sum of outputs.

12. Waveforms



Measurement points are given in [Table 9](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. Input A to output Y propagation delay times

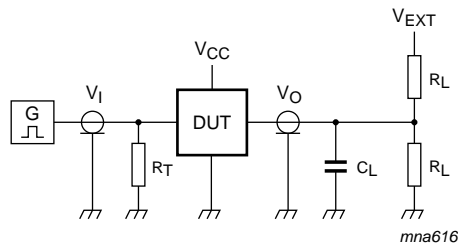


Measurement points are given in [Table 9](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. 3-state enable and disable times

Table 9. Measurement points

| Supply voltage | Input | Output | | |
|------------------|-------------|-------------|-------------------|-------------------|
| V_{CC} | V_M | V_M | V_X | V_Y |
| 1.65 V to 1.95 V | $0.5V_{CC}$ | $0.5V_{CC}$ | $V_{OL} + 0.15 V$ | $V_{OH} - 0.15 V$ |
| 2.3 V to 2.7 V | $0.5V_{CC}$ | $0.5V_{CC}$ | $V_{OL} + 0.15 V$ | $V_{OH} - 0.15 V$ |
| 2.7 V | 1.5 V | 1.5 V | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ |
| 3.0 V to 3.6 V | 1.5 V | 1.5 V | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ |
| 4.5 V to 5.5 V | $0.5V_{CC}$ | $0.5V_{CC}$ | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ |



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 10. Test circuit for measuring switching times

Table 10. Test data

| Supply voltage | Input | | Load | | V_{EXT} | | |
|------------------|----------|---------------|-------|--------------|--------------------|--------------------|--------------------|
| V_{CC} | V_I | t_r, t_f | C_L | R_L | t_{PLH}, t_{PHL} | t_{PZH}, t_{PHZ} | t_{PZL}, t_{PLZ} |
| 1.65 V to 1.95 V | V_{CC} | ≤ 2.0 ns | 30 pF | 1 k Ω | open | GND | $2V_{CC}$ |
| 2.3 V to 2.7 V | V_{CC} | ≤ 2.0 ns | 30 pF | 500 Ω | open | GND | $2V_{CC}$ |
| 2.7 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | 6 V |
| 3.0 V to 3.6 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | 6 V |
| 4.5 V to 5.5 V | V_{CC} | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | $2V_{CC}$ |

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

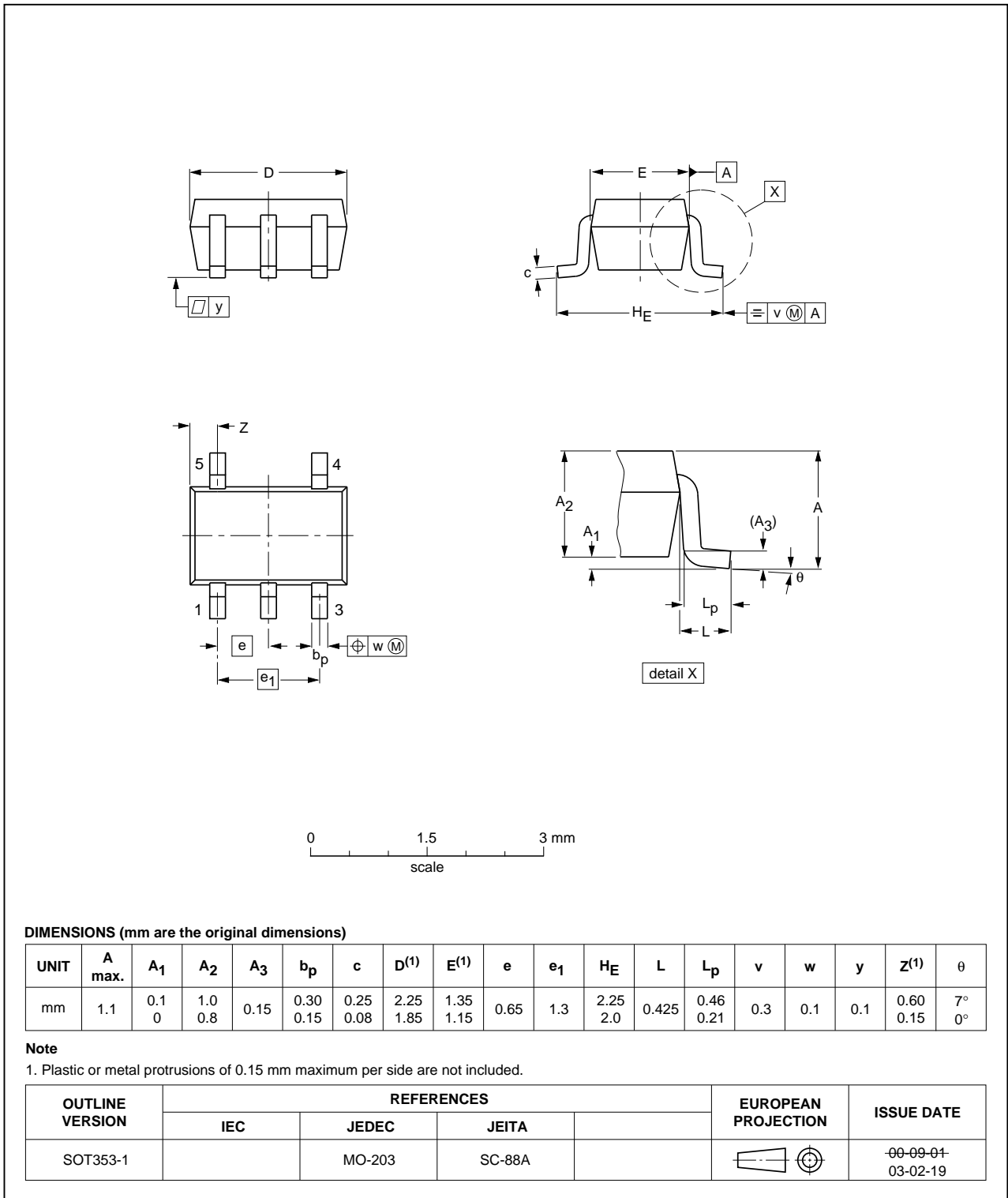


Fig 11. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

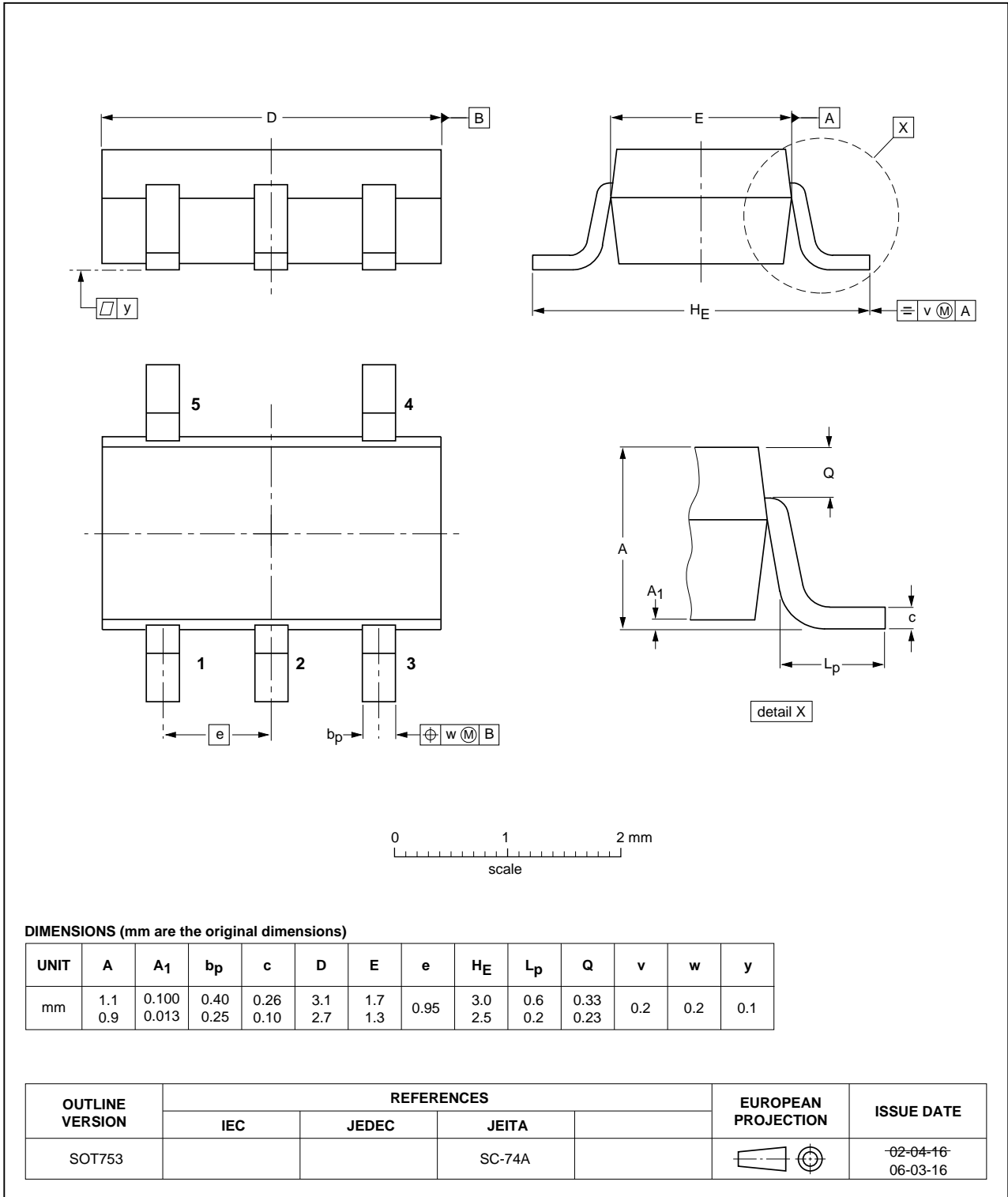


Fig 12. Package outline SOT753

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

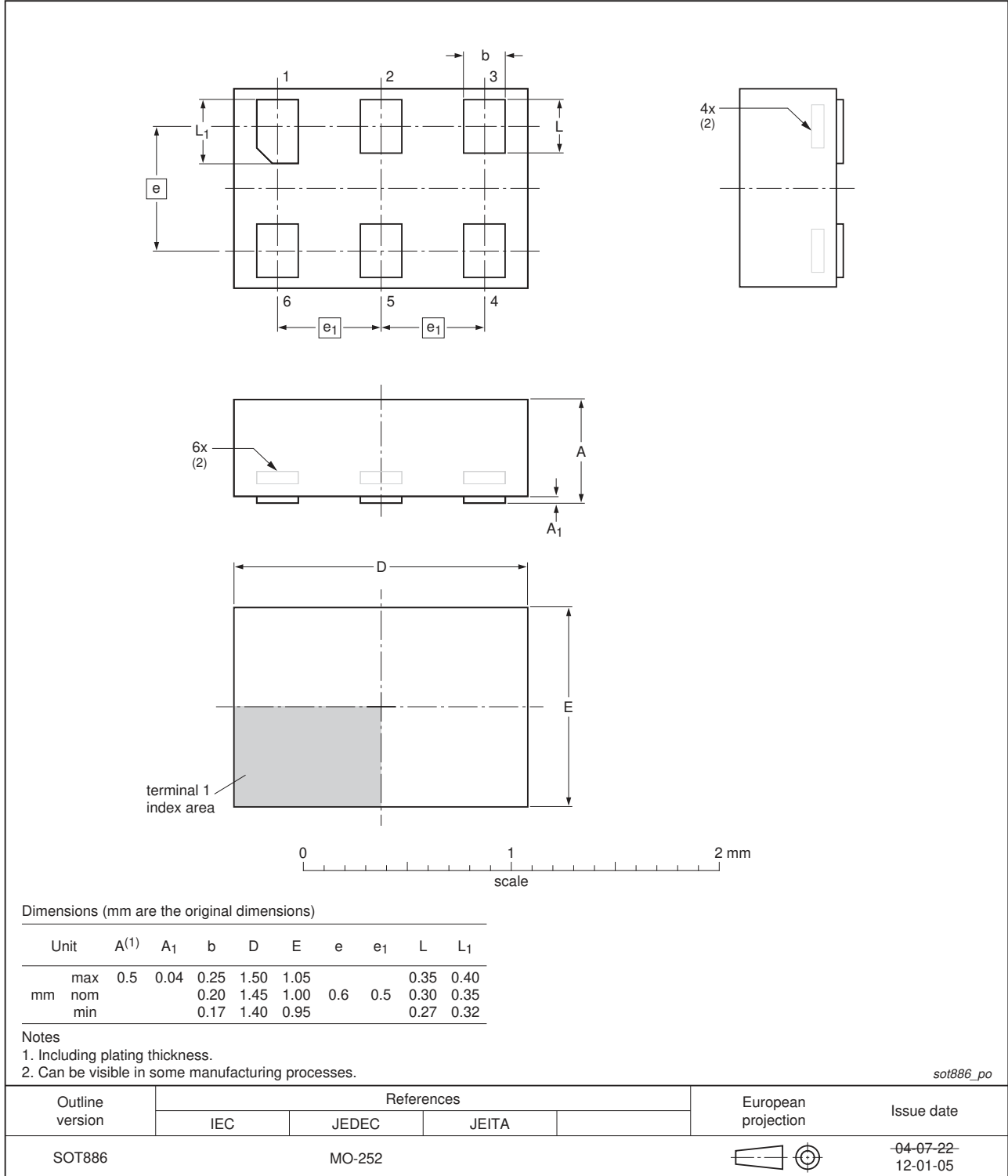


Fig 13. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

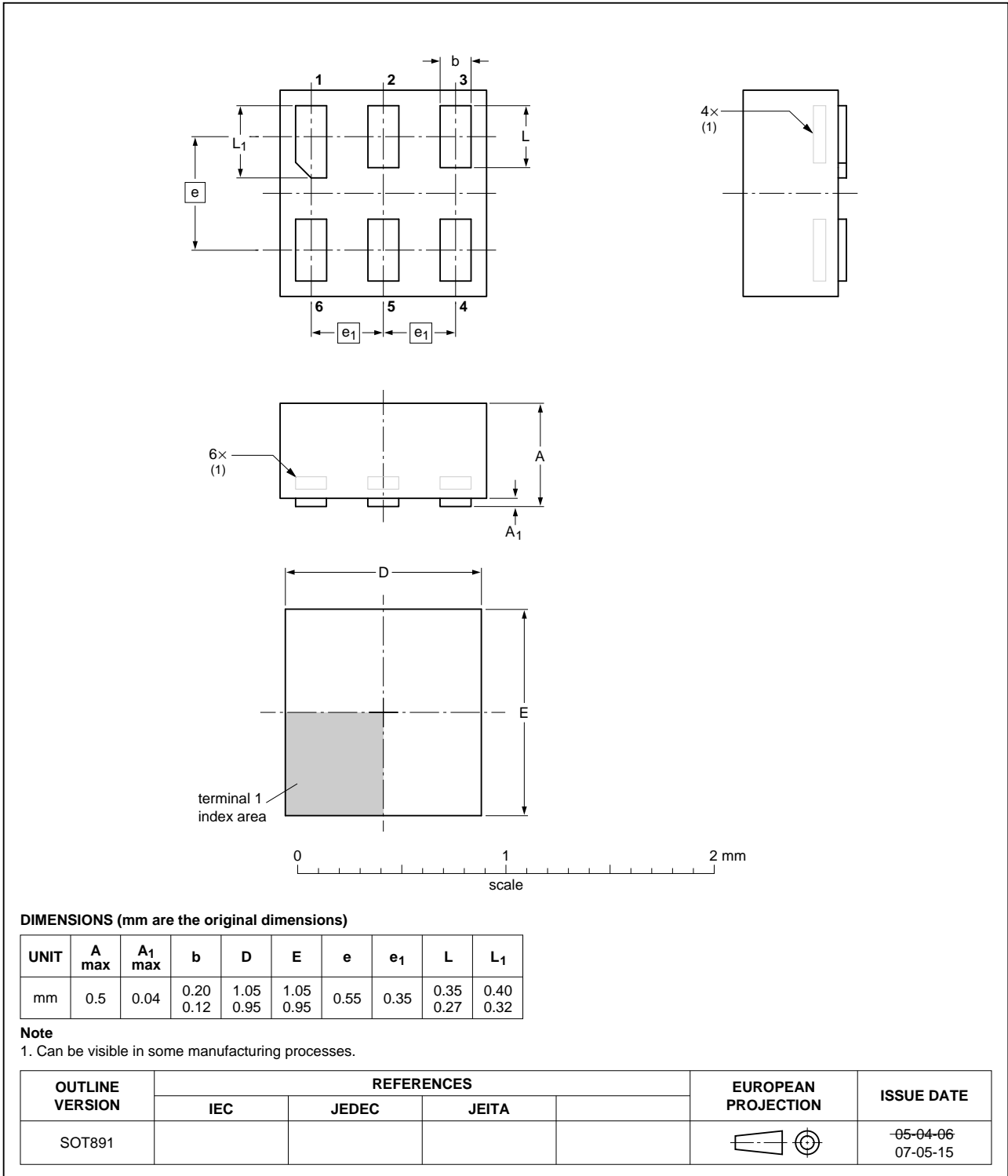


Fig 14. Package outline SOT891 (XSON6)

**XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm**

SOT1115

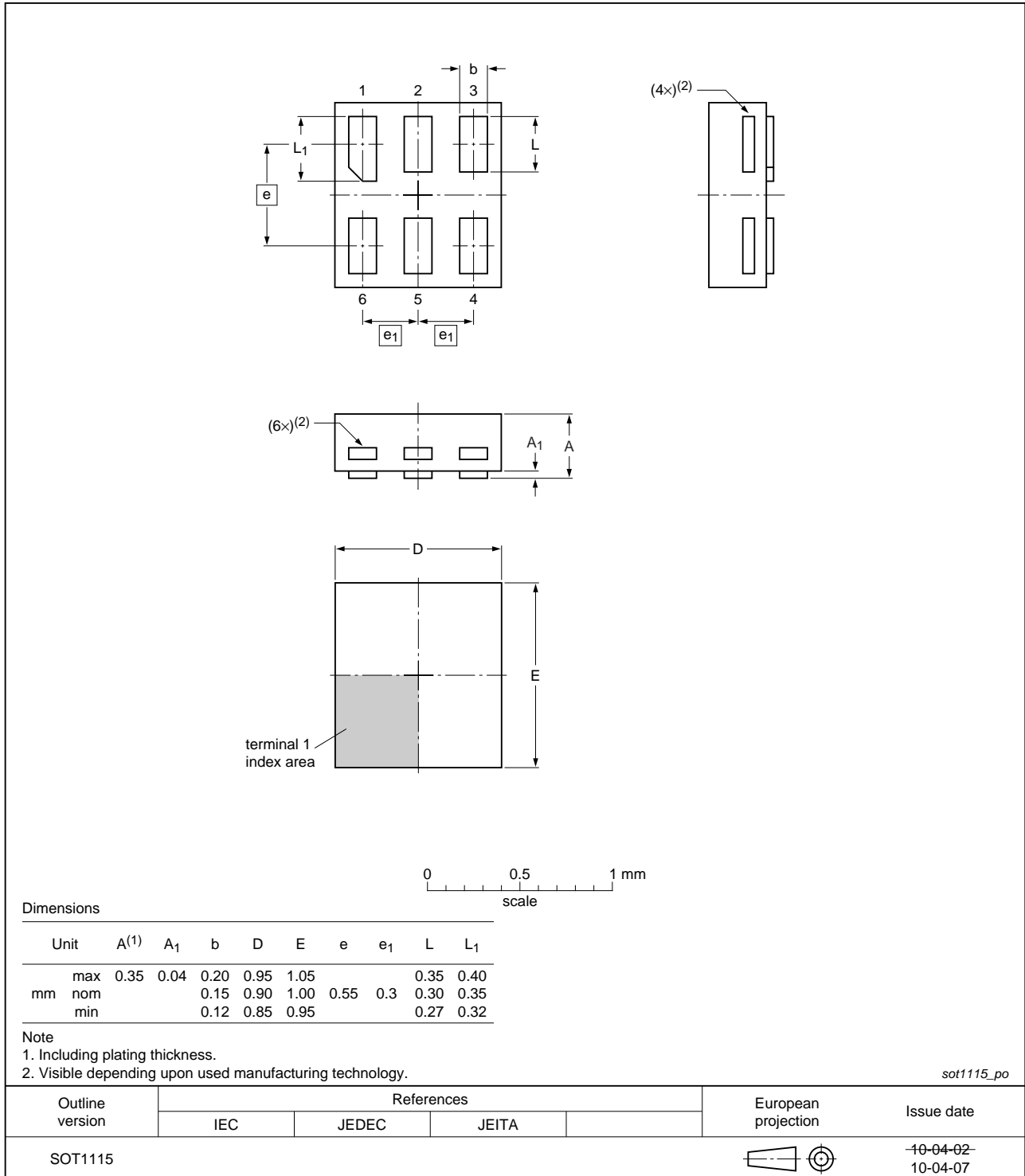


Fig 15. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm

SOT1202

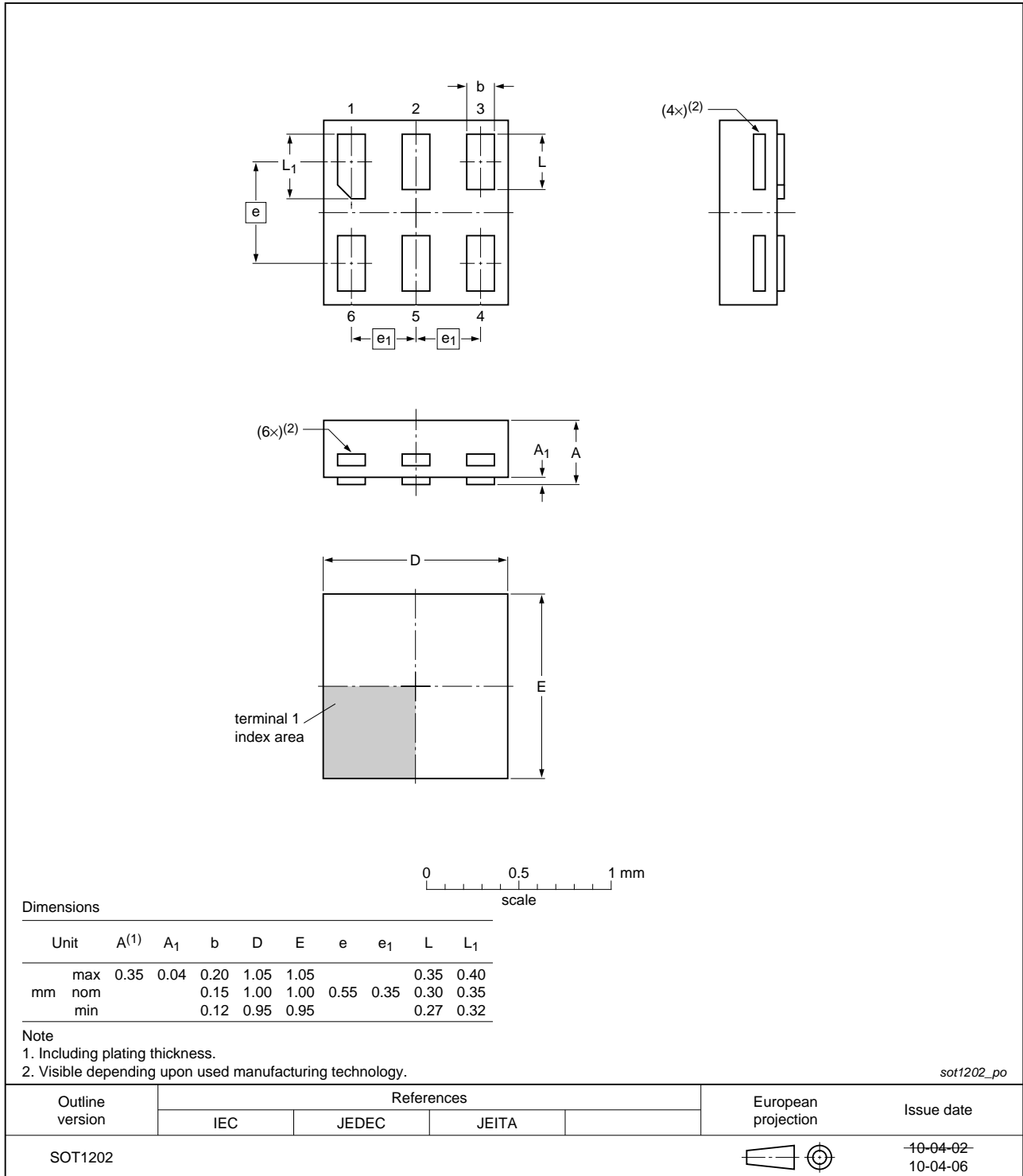


Fig 16. Package outline SOT1202 (XSON6)

X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;
5 terminals; body 0.8 x 0.8 x 0.35 mm

SOT1226

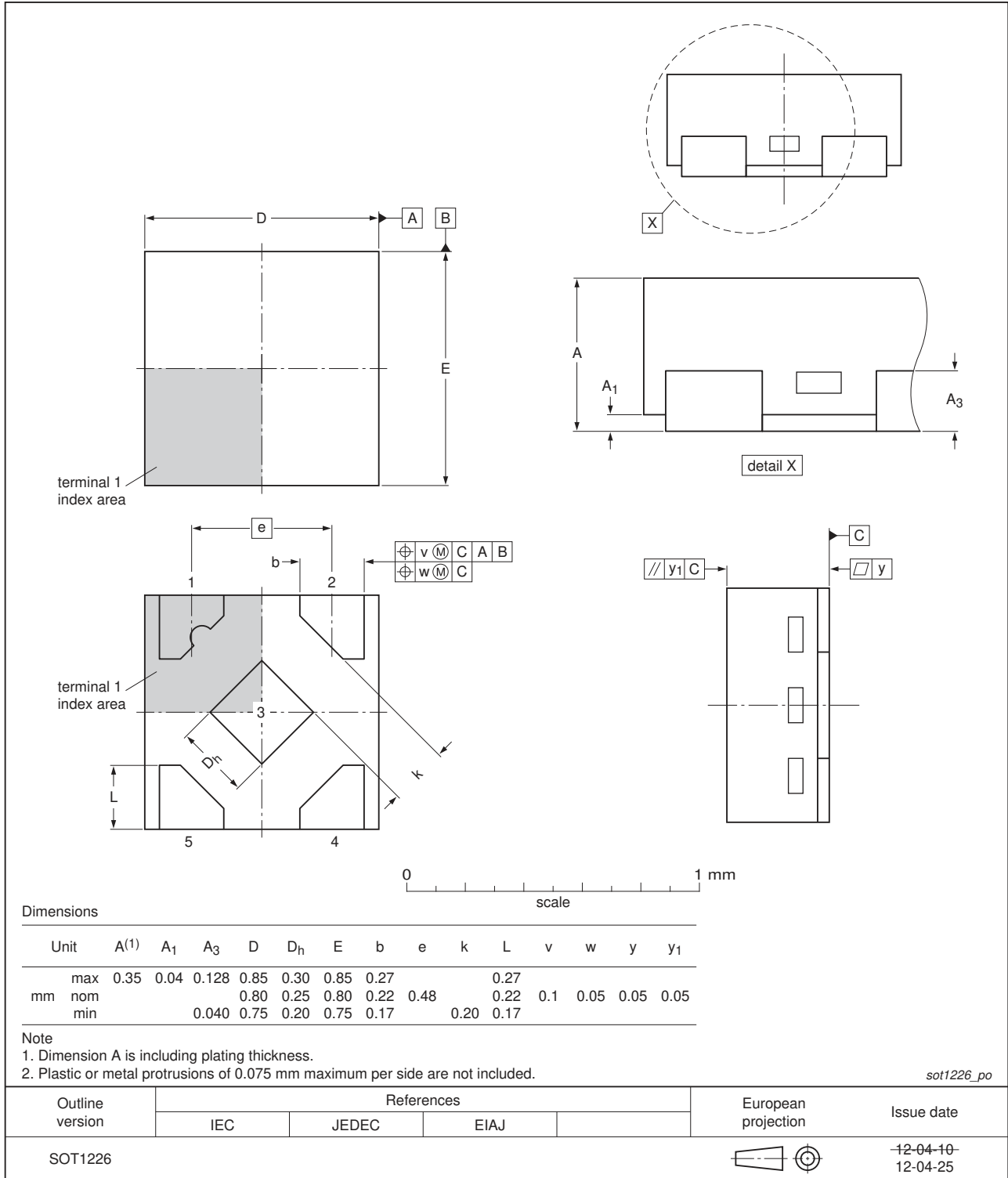


Fig 17. Package outline SOT1226 (X2SON5)

14. Abbreviations

Table 11. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |
| TTL | Transistor-Transistor Logic |

15. Revision history

Table 12. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|---|-----------------------|---------------|-----------------|
| 74LVC1G125 v.11 | 20120702 | Product data sheet | - | 74LVC1G125 v.10 |
| Modifications: | <ul style="list-style-type: none"> Added type number 74LVC1G125GX (SOT1226) Package outline drawing of SOT886 (Figure 13) modified. | | | |
| 74LVC1G125 v.10 | 20111207 | Product data sheet | - | 74LVC1G125 v.9 |
| Modifications: | <ul style="list-style-type: none"> Legal pages updated. | | | |
| 74LVC1G125 v.9 | 20101229 | Product data sheet | - | 74LVC1G125 v.8 |
| 74LVC1G125 v.8 | 20100824 | Product data sheet | - | 74LVC1G125 v.7 |
| 74LVC1G125 v.7 | 20070830 | Product data sheet | - | 74LVC1G125 v.6 |
| 74LVC1G125 v.6 | 20060912 | Product data sheet | - | 74LVC1G125 v.5 |
| 74LVC1G125 v.5 | 20040915 | Product specification | - | 74LVC1G125 v.4 |
| 74LVC1G125 v.4 | 20021118 | Product specification | - | 74LVC1G125 v.3 |
| 74LVC1G125 v.3 | 20020528 | Product specification | - | 74LVC1G125 v.2 |
| 74LVC1G125 v.2 | 20010406 | Product specification | - | 74LVC1G125 v.1 |
| 74LVC1G125 v.1 | 20001222 | Product specification | - | - |

16. Legal information

16.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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